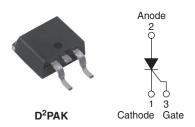




Vishay Semiconductors

Surface Mountable Phase Control SCR, 16 A



PRODUCT SUMMARY				
V _T at 16 A	< 1.25 V			
I _{TSM}	300 A			
V _{RRM}	800 V to 1600 V			

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Compliant to RoHS directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition
- Designed and qualified for industrial level





ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 µm) copper	3.5	5.5			
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	А		
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0			

Note

• $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	16	Λ		
I _{RMS}		25	Α		
V_{RRM}/V_{DRM}		800 to 1600	V		
I _{TSM}		300	А		
V_{T}	16 A, T _J = 25 °C	1.25	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
T _J		- 40 to 125	°C		

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA			
VS-25TTS08SPbF	800	800				
VS-25TTS12SPbF	1200	1200	10			
VS-25TTS16SPbF	1600	1600				

Document Number: 94383 Revision: 09-Jun-10 For technical questions within your region, please contact one of the following: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		LINUTO
PARAMETER	STWIDOL			TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	T _C = 93 °C, 180° conduction half sine wave 16		6	
Maximum RMS on-state current	I _{RMS}			2	5	Α
Maximum peak, one-cycle,	L	10 ms sine pulse,	rated V _{RRM} applied	300		_ ^
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	3	50	1
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V _{RRM} applied		450		A ² s
Waximum i-t for fusing	I−ι	10 ms sine pulse,	no voltage reapplied	63	30	A-5
Maximum $I^2\sqrt{t}$ for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied		63	00	A²√s
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C		1.	25	V
On-state slope resistance	r _t	- T _J = 125 °C		12	2.0	mΩ
Threshold voltage	V _{T(TO)}			1.0		.0
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 25 °C	V Detect V A	0.5		-
Maximum reverse and direct leakage current		T _J = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$	10		
Holding current	I _H	VS-25TTS08, VS-25TTS12	Anode supply = 6 V,	-	100	mA
		VS-25TTS16	resistive load, initial I _T = 1 A	100	150	
Maximum latching current	IL	Anode supply = 6 V, resistive load		200		
Maximum rate of rise of off-state voltage	dV/dt			50	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			1:	50	A/µs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0	VV
Maximum peak positive gate current	+ I _{GM}		1.5	Α
Maximum peak negative gate voltage	- V _{GM}		10	V
		Anode supply = 6 V, resistive load, T _J = - 10 °C	60	
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	45	mA
		Anode supply = 6 V, resistive load, T _J = 125 °C	20	
		Anode supply = 6 V, resistive load, T _J = - 10 °C	2.5	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125 ^{\circ}\text{C}, V_{DRM} = \text{Rated value}$ 0.25 2.0		
Maximum DC gate current not to trigger	I _{GD}			mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T 105 °C	4	μs
Typical turn-off time	t _q	T _J = 125 °C	110	



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C	
Soldering temperature	Ts	For 10 s (1.6 mm from case)	240		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W	
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} (1)		40	-C/VV	
Approximate weight			2	g	
Approximate weight			0.07	OZ.	
			25TT:	S08S	
Marking device		Case style D ² PAK (SMD-220)	25TTS12S		
			25TT:	S16S	

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W For recommended footprint and soldering techniques refer to application note #AN-994

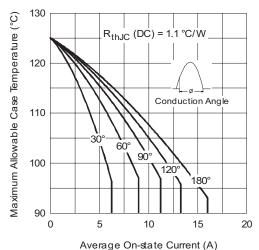


Fig. 1 - Current Rating Characteristics

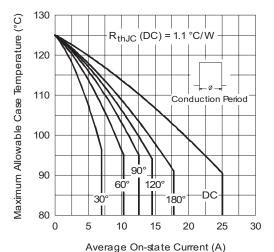


Fig. 2 - Current Rating Characteristics

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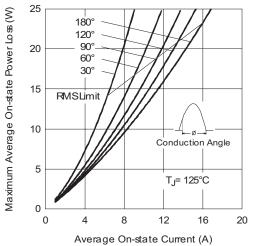


Fig. 3 - On-State Power Loss Characteristics

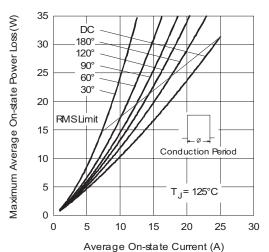
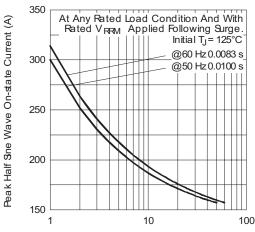


Fig. 4 - On-State Power Loss Characteristics



Number Of Equal Amplitude Half Cycle Current Pulæs(N)

Fig. 5 - Maximum Non-Repetitive Surge Current

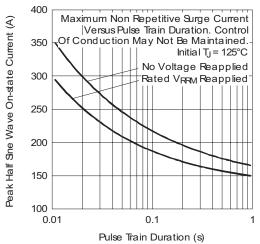


Fig. 6 - Maximum Non-Repetitive Surge Current

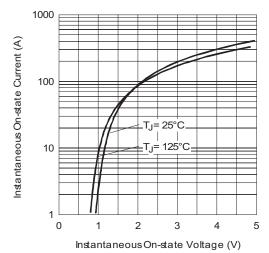


Fig. 7 - On-State Voltage Drop Characteristics



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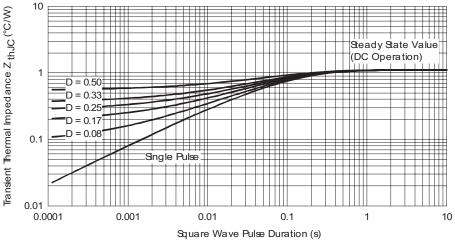


Fig. 8 - Gate Characteristics

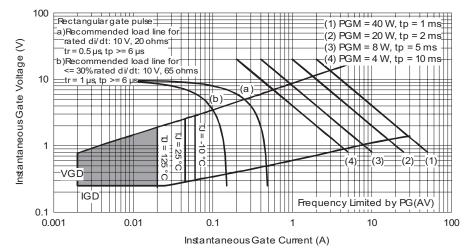


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

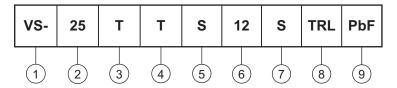
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ORDERING INFORMATION TABLE

Device code



- 1 HPP product suffix
- 2 Current rating (25 = 25 A)
- Circuit configuration:
 - T = Single thyristor
- 4 Package:
 - T = TO-220AC
- 5 Type of silicon:
 - S = Standard recovery rectifier
- 08 = 800 V 12 = 1200 V
- Voltage rating: Voltage code x 100 = V_{RRM} S = TO-220 D²PAK (SMD-220) version
- 16 = 1600 V

- 8 • None = Tube
 - TRL = Tape and reel (left oriented)
 - TRR = Tape and reel (right oriented)
- 9 PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95046</u>				
Part marking information	www.vishay.com/doc?95054			
Packaging information	www.vishay.com/doc?95032			

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